

SWITCHING DIODES

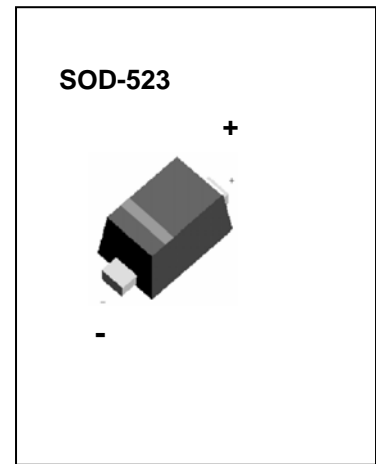
PRODUCT SUMMARY

SOD-523 Plastic-Encapsulate Diodes

FEATURES

Small surface mounting type
High switching speed

 **Pb-free; RoHS-compliant**



MARKING: 61

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

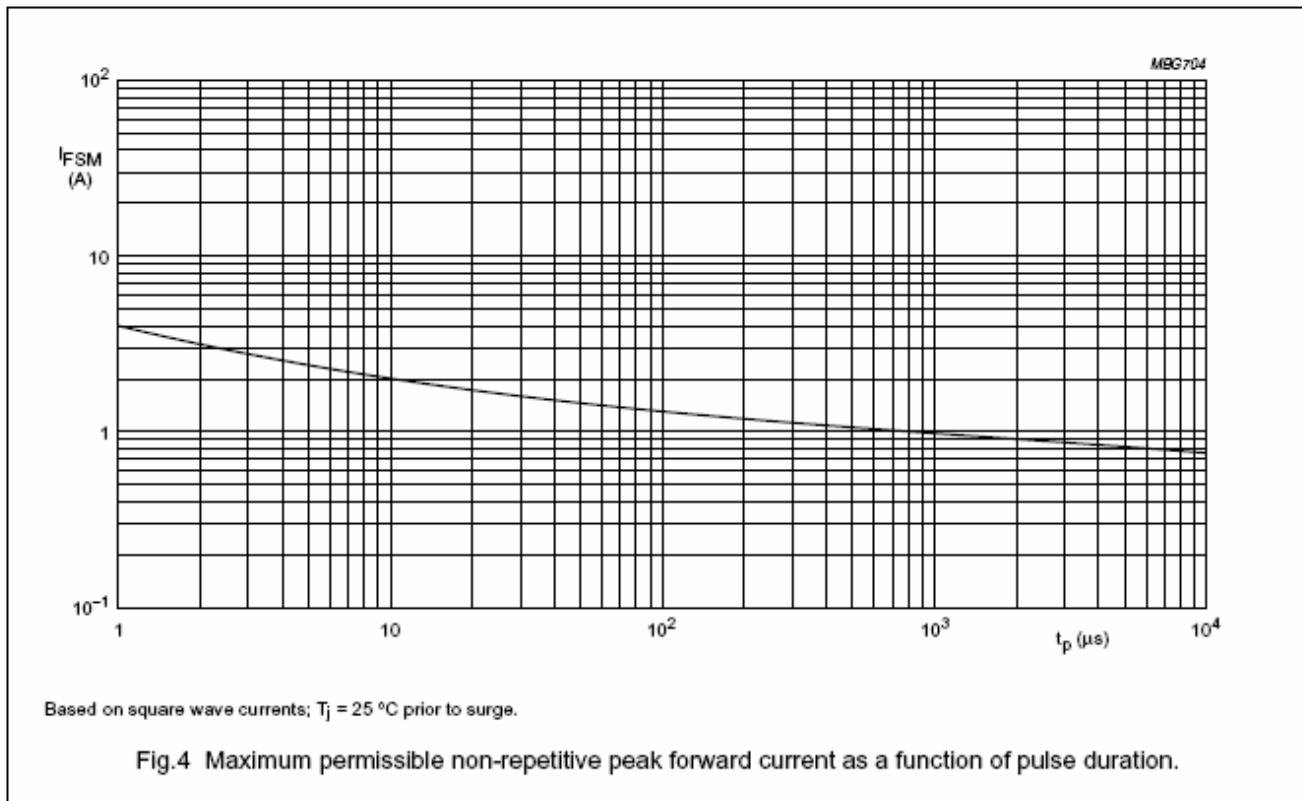
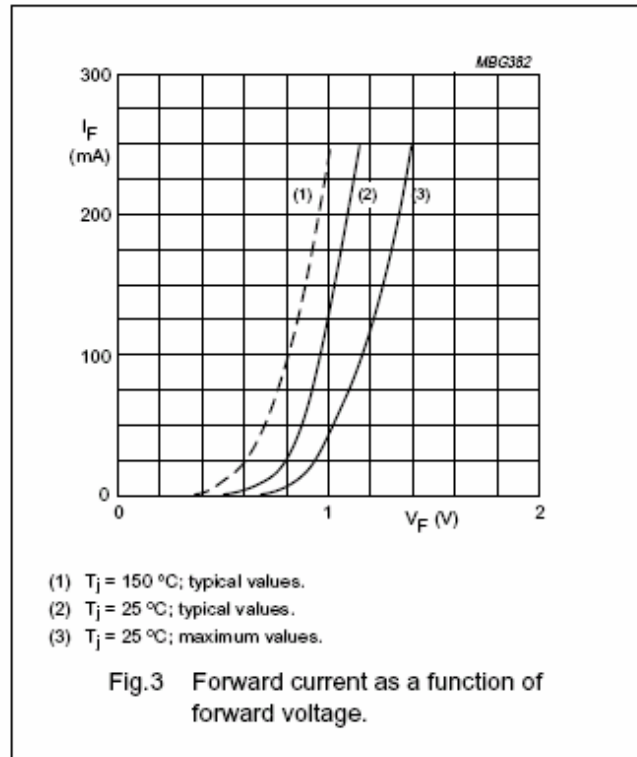
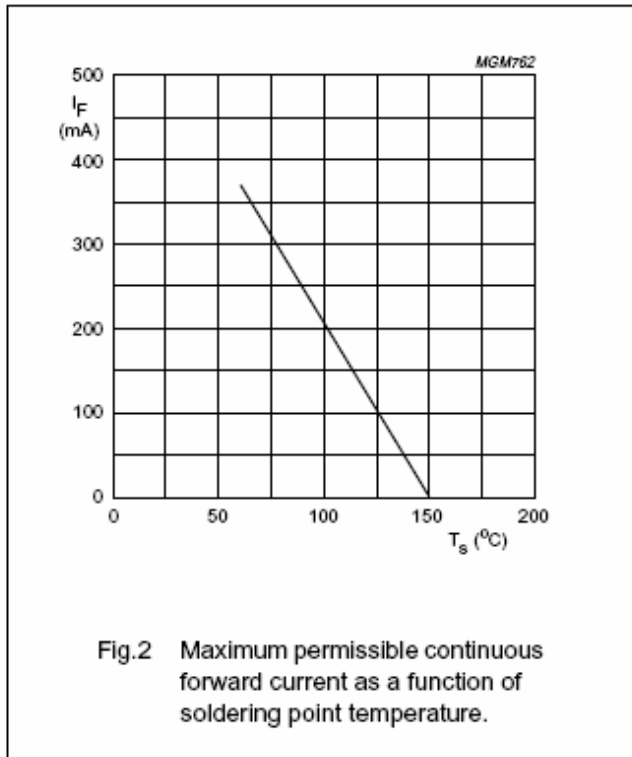
Single Diode @ $T_A=25^{\circ}\text{C}$

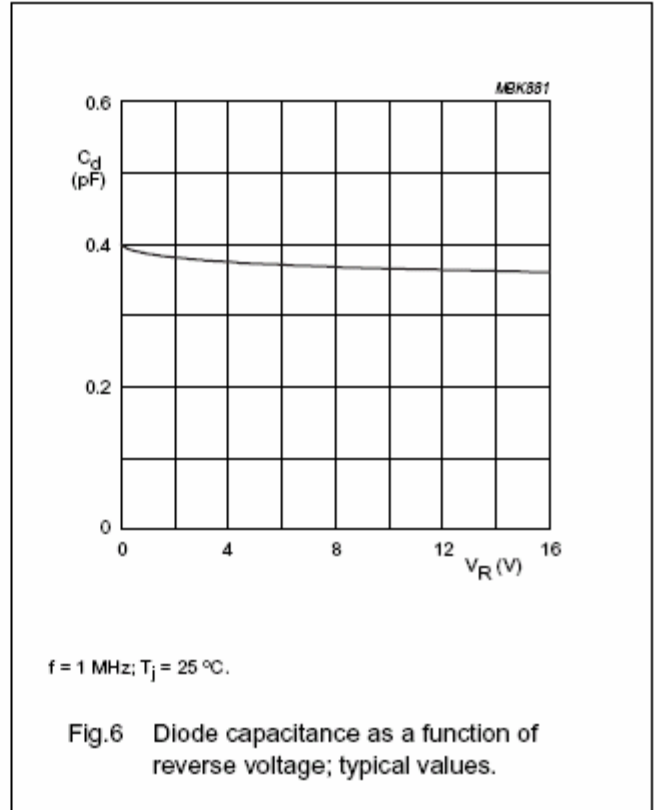
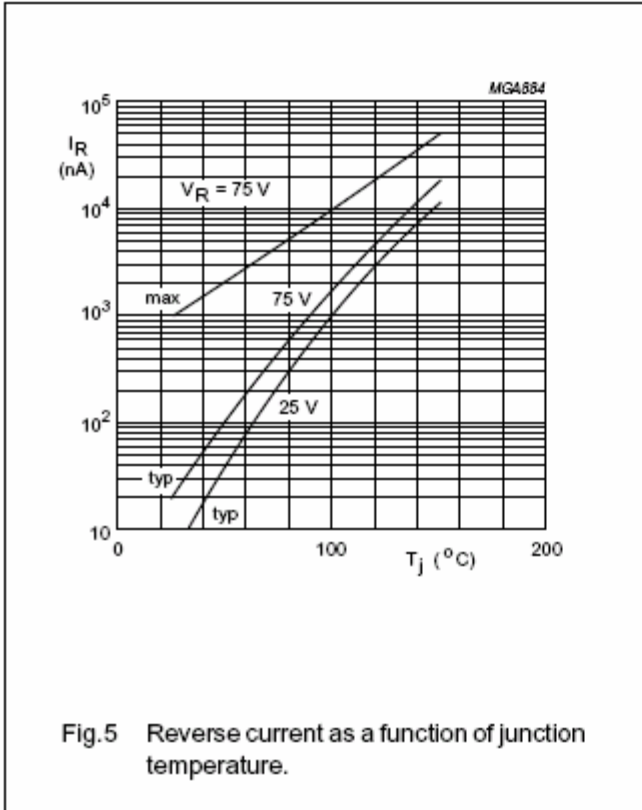
Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	75	V
Mean rectifying current	I_O	250	mA
Peak forward surge current	I_{FSM}	0.5	A
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-65~+150	$^{\circ}\text{C}$

ELECTRICAL RATINGS @ $T_A=25^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.715 0.855 1 1.25	V	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=50\text{mA}$ $I_F=150\text{mA}$
Reverse current	I_R			0.03 1	μA	$V_R=25\text{V}$ $V_R=75\text{V}$
Capacitance between terminals	C_T			1	pF	$V_R=0$, $f=1\text{MHZ}$
Reverse recovery time	t_{rr}			4	ns	$I_F=10\text{mA}$, $R_L=100\Omega$

TYPICAL CHARACTERISTICS





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